

ABSTRACT

A method for manufacturing a semiconductor device of the present invention includes at least the following three steps. A step (A) of preparing a structure including a semiconductor wafer having a circuit-formed surface and an adhesive film (100) attached to the circuit-formed surface side of the semiconductor wafer. A step (B) of back grinding a surface on a side opposite to the circuit-formed surface side of the semiconductor wafer. A step (C) of radiating ultraviolet rays to the adhesive film (100) and then removing the adhesive film (100) from the semiconductor wafer. In addition, as the adhesive film (100), an adhesive film having a base material layer (10), an antistatic layer (30), and an adhesive resin layer (40) including a conductive additive in this order is used, and the adhesive film is used so that the adhesive resin layer (40) faces the circuit-formed surface side of the semiconductor wafer.